In its

OFFICE OF NAVAL RESEARCH

Contract N00014-82-K-0280

Task No. NR413E001

TECHNICAL REPORT NO. 34

Dissociative Adsorption of Ph₃ on Si(111)-(7x7) - A High Resolution Electron Energy Loss Spectroscopy Study

by

P.J. Chen, M.L. Colaianni, R.M. Wallace and J.T. Yates, Jr.

Submitted to

Surface Science

Surface Science Center Department of Chemistry University of Pittsburgh Pittsburgh, PA 15260 DTIC ELECTE AUG 17 1990 B

August 7, 1990

Reproduction in whole or in part is permitted for any purpose of the United States Government

This document had been approved for public release and sale; its distribution is unlimited

SECURITY CLASSIFICATION OF THIS PAGE (When Data Entered)						
REPORT DOCUMENTATION PAGE		READ INSTRUCTIONS BEFORE COMPLETING FORM				
I. REPORT NUMBER	2. GOVT ACCESSION NO.	3. RECIPIENT'S CATALOG NUMBER				
34						
4. TITLE (and Subtitio)	L	5. TYPE OF REPORT & PERIOD COVERED				
Dissociative Adsorption of PH_3 on $Si(111)$ - $(7x7)$						
- A High Resolution Electron Energy Loss						
Spectroscopy Study		6. PERFORMING ORG. REPORT NUMBER				
7. Aufigrachen, M.L. Colaianni, R.M. Wa	llace and	8. CONTRACT OR GRANT NUMBER(*)				
J.T. Yates, Jr.						
	······································					
9. PERFORMING ORGANIZATION NAME AND ADDRESS		10. PROGRAM ELEMENT, PROJECT, TASK AREA & WORK UNIT NUMBERS				
Department of Chemistry						
University of Pittsburgh		!				
Pittsburgh, PA 15260						
11. CONTROLLING OFFICE NAME AND ADDRESS		August 7, 1990				
		13. NUMBER OF PAGES				
14. MONITORING AGENCY NAME & ADDRESS(II dilleren	t from Controlling Office)	15. SECURITY CLASS. (of this report)				
		Unclassified				
		15a. DECLASSIFICATION/DOWNGRADING SCHEDULE				
16. DISTRIBUTION STATEMENT (of this Report)						
		:				
17. DISTRIBUTION STATEMENT (of the abstract entered	in Block 20, it different from	m Report)				
18. SUPPLEMENTARY NOTES						
		İ				
• •						
19. KEY WORDS (Continue on saverse side if necessary and identity by block number)						
Phosphine, Silicon(111), Doping, Phosphorus, Dissociative						
÷ β		,				

20. ABSTRACT

Dissociative adsorption of PH3 on S1(111)-(7x7) has been observed at 80 K. The S1-H species is observed to be produced upon PH3 adsorption. Depending upon the PH3 surface coverage, $PH_3(a)$ (minority species) and $PH_2(a)$ species are found on the surface. The thermal dissociation of the surface PH2 species occurs between 450 and 500 K, resulting in the capture of hydrogen and phosphorus on the surface.

DO 1700 1473

EDITION OF 1 NOV 65 IS OBSOLETE

Submitted to: Surface Science

Date: 7 August 1990

Dissociative Adsorption of PH_3 on Si(111)-(7x7) - A High Resolution Electron Energy Loss Spectroscopy Study

P.J. Chena), M.L. Colaianni, R.M. Wallaceb) and J.T. Yates, Jr.

Surface Science Center Department of Chemistry University of Pittsburgh Pittsburgh, PA 15260 Dissociative Adsorption of PH3 on Si(111)-(7x7) - A High Resolution Electron Energy Loss Spectroscopy Study

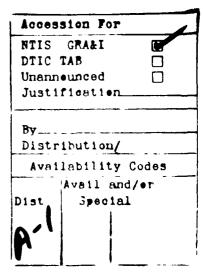
P.J. Chena), M.L. Colaianni, R.M. Wallaceb) and J.T. Yates, Jr.

Surface Science Center Department of Chemistry University of Pittsburgh Pittsburgh, PA 15260

Abstract

Dissociative adsorption of PH3 on Si(111)-(7x7) has been observed at 80 K. The Si-H species is observed to be produced upon PH3 adsorption. Depending upon the PH3 surface coverage, PH3(a) (minority species) and PH2(a) species are found on the surface. The thermal dissociation of the surface PH2 species occurs between 450 and 500 K, resulting in the capture of hydrogen and phosphorus on the surface.

- a) Department of Physics, University of Pittsburgh.
- b) Materials Science Laboratory, Texas Instruments Inc., Dallas, TX 75265





I. Introduction

Studies of simple hydride molecules (NH3, PH3, C2H2, C2H4, C3H6, B2H6, etc.) on silicon surfaces have received increasing attention in recent years [1-17] due to the involvement of molecules of this type in chemical vapor deposition (CVD) and doping of silicon. Vibrational spectroscopy is among the variety of surface analytical methods being applied to selected molecule/Si surface systems to monitor the adsorption and dissociation processes $\lceil 6.7.11-13 \rceil$. In the relatively well-studied system of NH2 on Si surfaces, high resolution electron energy loss spectroscopy (HREELS) studies [11-13] have provided direct evidence for the dissociative adsorption of NH3 on both Si(111) and Si(100). For the analogous molecule PH3, however, such important information is not available, although rather detailed studies have been carried out using LEED. Auger electron spectroscopy (AES), X-ray photoelectron spectroscopy (XPS), secondary ion mass spectroscopy (SIMS) [1-5], and recently, temperature programmed desorption (TPD), kinetic uptake measurements and electron stimulated desorption (ESD) [16,17]. We present here a HREELS study of PH3 adsorption and its thermal behavior on the Si(111)-(7x7) surface. Vibrational evidence for dissociative adsorption of adsorbed PH3 species has been obtained at 80 K, confirming the results of other studies using other experimental methods at this temperature [16,17]. Additional P-H bond scission occurs at ~450 K; this is followed by H₂ desorption (~740 K) and P2 desorption (~1000 K).

II. Experimental

The experiments were performed in a stainless steel UHV system described previously [18]. The typical system base pressure was ~1x10⁻¹⁰ mbar as measured with a Bayard-Albert ionization gauge. The UHV system is equipped with a single

pass CMA Auger electron spectrometer (AES) (Perkin-Elmer), a shielded quadrupole mass spectrometer (QMS) and a home built LEED apparatus. High resolution electron energy loss spectroscopy (HREELS) studies were conducted with a Leybold-Heraeus ELS-22 spectrometer interfaced to a digital data acquisition system [19]. The incident electron energy was ~6.5 eV and the total scattering angle was about 120°.

The Si(111) used in this study was a 13mm x 13mm x1.5mm, p-type, B-doped (10 ohm-cm nominal resistivity) single crystal oriented to within 1°. The crystal was cooled by liquid-N₂ to 80 K and could be resistively heated up to 1300 K as measured by a W/Re(5%)-W/Re(26%) thermocouple. The mounting and initial cleaning of the crystal using a standard chemical cleaning procedure is described elsewhere [16,20]. The final cleaning and preparation of the surface was achieved by Ar⁺ sputtering at an energy of 1 keV and a current of 3 μ A, followed by subsequent annealing at 1200 K and then, slow cooling back to 80 K. This procedure produces a well-ordered Si(111)-(7x7) surface with no impurities within the detection limit of AES.

The adsorption of phosphine gas was accomplished by using a translatable microcapillary array doser [20] contained in the UHV system. The PH₃ flux at the crystal was calibrated in the same fashion as described in a recent paper [17] by using the doser-crystal geometry and the PH₃ effusion rate into the doser. Correlation of the <u>absolute</u> full coverage for PH₃ adsorption in this apparatus with that measured elsewhere [17] was made to within 8% accuracy. It is determined that this full coverage corresponds to 1.9x10¹⁴ PH₃ cm⁻². This full (saturation) coverage may be achieved after an exposure of 2x10¹⁵ PH₃ cm⁻² at 80 K [17]. To avoid any possible electron beam induced decomposition and electron stimulated desorption (ESD) effects during PH₃ adsorption, the ionization sources (ionization gauge, QMS) were turned off.

III. Results and discussion

1. Phosphine adsorption on Si(111)-(7x7) at 80 K

Detailed kinetic studies of phosphine adsorption on Si(111)-(7x7) at 120 K have been reported in separate papers [16,17]. Uptake measurements show that phosphine adsorption proceeds with a constant sticking probability (S=1) up to 1.5x10¹⁴ PH₃ molecules cm⁻² (i.e. ~75% of the saturation coverage), indicating an extrinsic mobile precursor adsorption mechanism. Additional PH₃ adsorbs with reduced sticking probability until saturation is reached at 1.9x10¹⁴ PH₃ molecules cm⁻². Similar PH₃ uptake experiments conducted in this work at 80 K agree well with the above results, where an independent absolute calibration of the doser in this apparatus has been made.

Figure 1 shows the HREEL spectra from the clean and PH₃-exposed Si(111)-(7x7) surface under specular electron scattering conditions. It is well known that the clean Si(111)-(7x7) surface exhibits a broad, temperature dependent, energy loss tail which is associated with the Si(111)-(7x7) surface electronic structure (see Fig. 1(a)) [21]. Upon PH₃ adsorption, this broad energy loss tail is removed (Fig. 1(b)-(e)). For the PH₃-covered surface, energy losses are observed at 495, 600, 1050, 2060 and 2260 cm⁻¹. The 2060 cm⁻¹ mode is readily identified as the Si-H stretching mode, ν (SiH), by comparison with the now well-known H/Si(111) system [22], and its presence is thus indicative of PH₃ dissociation upon adsorption at 80 K. The shoulder at ~600 cm⁻¹ is the corresponding Si-H bending mode, δ (SiH), in the monohydride phase. Detailed assignments will be given to all the modes in the following paragraphs.

There is other experimental evidence indicating some dissociation of PH_3 into PH_X ($2 \ge x \ge 1$) species on Si(111)-(7x7) at low temperatures based on recent Auger electron spectroscopy studies [16]. In this work, the silicon bulk

plasmon loss feature accompanying the 92 eV Si(LVV) Auger transition exhibits changes characteristic of the presence of chemisorbed H after PH $_3$ adsorption at 120 K. This change in the plasmon loss intensity is enhanced upon warming of the surface to ~500 K as further P-H bond scission occurs [16]. The HREELS observation of the presence of the Si-H stretching mode upon PH $_3$ adsorption provides conclusive evidence for dissociative adsorption. However, in order to further identify the surface PH $_X$ (a) species, it is informative to compare our measurements with some infrared (IR) and HREELS data for certain systems containing PH $_3$, PH $_2$ and PH moieties. A selective list of results is shown in Table I.

HREELS studies of PH3 chemisorbed on Pt(111) by Mitchell et al [23] show the PH₃ stretching frequency at 2325 cm $^{-1}$ and the two PH₃ deformation modes (symmetric and asymmetric) at $\delta_s = 985 \text{ cm}^{-1}$ and $\delta_d = 1080 \text{ cm}^{-1}$ (non-dipole active) respectively. On the other hand, IR studies of PH2-containing compounds (silyl and methyl phosphine, SiH3PH2, CH3PH2, diphosphine, P2H4 [25], and silanyl phosphine, Si₂H₅PH₂ [26]) report a PH₂ deformation (scissors) mode $\delta(PH_2)$ in the range 1069 - 1093 cm⁻¹, a PH₂ stretching mode, $v_s(PH_2)$, in the range 2300 - 2310 cm⁻¹, and a Si-P stretching mode, v(SiP), in the range 454 -515 cm $^{-1}$. Based upon these known frequencies, we assign the 495 cm $^{-1}$ mode in our HREEL spectra as the Si-P streching mode, v(SiP). The vibrational modes at 1050 and 2260 cm $^{-1}$ are assigned to surface PH₂(a) species, with some possible contribution by $PH_3(a)$. In particular, the 1050 cm⁻¹ mode can belong to the scissors deformation mode of the $PH_2(a)$, $\delta(PH_2)$, with a possible contribution from the (positively-shifted) symmetric deformation mode of the $PH_3(a)$, $\delta_s(PH_3)$, since off-specular measurements (not shown) indicate that it is due to dipole scattering and its frequency is not a decisive indicator of its origin.

The following experimental facts are important in clarifying the identities

of the surface $PH_X(a)$ species: (1) the presence of the Si-H mode strongly suggests, even at 80 K, the dissociation of PH_3 , i.e. the presence of $PH_2(a)$ and/or PH(a) on the surface; (2) temperature programmed desorption (TPD) measurements from intermediate to saturation initial coverages of PH_3 on Si(111)-(7x7) [17] also reveal the desorption of small quantities of (non-recombinative) molecular $PH_3(g)$, indicating the presence of molecular $PH_3(a)$ on the surface. The surface concentration of the $PH_3(a)$ species, however, is believed to be rather low [17]. Therefore, for PH_3 coverages above $1.5x10^{14}$ cm⁻² where molecular PH_3 desorption can be detected by TPD, the coexistence of $PH_3(a)$ and $PH_2(a)$ species on Si(111) surface yields the observed energy loss features at 1050 and 2260 cm⁻¹. For PH_3 coverages below $1.5x10^{14}$ cm⁻², the predominant surface species is $PH_2(a)$ with very little or no $PH_3(a)$, although the spectroscopic evidence for this is not totally conclusive.

Another surface species candidate, PH(a), is not preferred in our interpretation of the HREEL spectra. A survey of infrared studies of PH-containing compounds shows that, unlike the PH₂-containing compounds, there is quite a variation in the observed P-H deformation frequency δ (PH). Some simple compounds such as (CH₃)₂PH and F₂PH exhibit P-H deformation frequencies at 998 cm⁻¹ and 1016 cm⁻¹ respectively [27,28]. Other PH ligands as in (CF₃)₂PH and (CF₃S)₂PH exhibit a much lower P-H deformation frequency at 850 cm⁻¹ and 894 cm⁻¹ [29] respectively. A variety of secondary phosphines containing substituted aryl (R₁) and phenyl (R₂) groups of the general formula R₁R₂PH also exhibit P-H deformation modes in the range 886-897 cm⁻¹ [30]. Assuming that δ (PH) modes in the 850-897 cm⁻¹ range are analogous to that of a PH species adsorbed on Si(111), we can eliminate PH(a) as a candidate species responsible for the 1050 cm⁻¹ mode in our HREEL spectra. Such an argument is further supported by the experimental observation that, upon total thermal decomposition

of the $PH_X(a)$ species, the intensity of the silicon-hydrogen stretching mode $\nu(SiH)$, undergoes more than a 3-fold increase compared to its initial intensity at 80 K (detail in next section). Considering the rather low initial concentration of surface hydrogen species H(a) at 80 K, such a large increase in H(a) can only be accounted for by the decomposition of $PH_2(a)$ species rather than PH(a). Of course, this does not exclude PH(a) from being a minority species on the surface at 80 K. Based upon the above discussions, we assign the 1050 cm⁻¹ mode as $\delta(PH_2)$.

HREELS studies of an analogous molecule, NH₃, on the Si(111)-(7x7) surface [11] have reached a similar conclusion that NH₃ dissociates into NH₂(a) and H(a) at 300 K. Additionally, electron stimulated desorption ion angular distribution (ESDIAD) and TPD studies of NH₃ chemisorbed on Si(100) have shown that NH₂ is the dominant surface species produced [14,15]. Therefore, the bonding of the PH₃(NH₃) molecules to the Si(111) surface occurs through the scission of one of the P-H(N-H) bonds instead of surface bonding through the phosphorus(nitrogen) lone pair electrons. This is in contrast to the case of PH₃(NH₃) bonding to metal surfaces [23,24] where undissociated bonding involving the lone pair electrons is found. Dangling bond site capping experiments involving atomic deuterium have demonstrated that the active sites for both PH₃ [17] and NH₃ [15] adsorption are the Si dangling bonds.

2. Thermal behavior of the phosphine-derived overlayer

As previously mentioned, thermal desorption studies of adsorbed phosphine on Si(111)-(7x7) reveal two reaction pathways (Figure 2). In the first pathway, molecularly adsorbed PH₃ desorbs as PH₃(g), forming a broad desorption feature extending to 550 K. The quantity of PH₃ desorbing is a small fraction of a monolayer [16,17]. In the second pathway, surface PH₂(a) species thermally

decompose ultimately into P(a) and H(a), which subsequently desorb as $P_2(g)$ and H₂(g). H₂ desorption is observed from 650 to 850 K with the peak temperature at ~740 K. P2 desorbs from 900 - 1100 K. In the current work, HREELS has also been used to monitor the thermal behavior of the surface PH2(a) species. Figure 3 shows the HREEL spectra taken at 80 K after sequentially heating the PH3-exposed Si(111) surface to specified temperatures. By heating in the temperature range of 80 - 450 K, an intensity decrease in the $v(PH_2)$ stretching mode at 2260 cm^{-1} signifies the breaking of additional P-H bonds. In the temperature range 450 - 500 K, by contrast, a major increase in the intensities of the Si-H stretching mode at 2070 $\rm cm^{-1}$ and Si-H deformation mode at 630 $\rm cm^{-1}$ is observed. Because of the large increase in the intensity of the Si-H stretching vibration after total thermal dissociation, it is likely that the majority species on the surface are $H(a) + PH_2(a)$ in the temperature range 80 -450 K rather than 2H(a) + PH(a). We do not understand why the $v(PH_2)$ mode seems to decrease in intensity mostly in the low temperature range; this may be due to a structural rearrangement on the surface. The decrease of intensity in the 1050 cm $^{-1}$ &(PH₂) mode, mainly in the temperature range 450 - 500 K, is also indicative of PH2 dissociation, possibly into PH(a) and H(a). However, based upon our HREELS data, we are unable to make a clear identification of the PH(a) species due to the likely overlap of its spectral features with those of PH2(a) and our limited instrumental resolution.

For a saturation PH3 exposure $(2x10^{15} \text{ molecules/cm}^2)$, it can be seen from comparison of Figure 2 and Figure 3 that the desorption of a small amount of molecular PH3(g) in the temperature range 80 - 550 K during heating does not seem to have a noticeable influence on the observed frequencies of the main spectral features, except for the background intensity increase observed between 80 and 200 K. The nature of this broad background increase in the HREEL spectra

after heating the PH₃-covered surface to 200 K is not currently understood. It has been consistently observed in all of our heating experiments with low and high initial PH₃ coverages. A similar background is also observed in our PH₃ adsorption studies at 300 K (discussed below). The possibility of surface contamination during the course of HREELS analysis can be ruled out by the fact that leaving an unheated overlayer in the UHV system for an extended length of time does not cause such a background increase. Therefore, we tentatively attribute this broad background to some unknown electronic transition processes associated with the PH₂(a) + H(a)/Si(111) layer.

Significant changes in HREEL spectra occur between 450 and 500 K where the two Si-H vibrational modes at 630 and 2070 cm $^{-1}$ dominate the spectrum after heating to 500 K. Complete dissociation of the PH₂(a) species into P(a) and H(a) occurs in the above temperature range. This behavior, in which additional Si-H species are produced, corresponds closely to the results of AES lineshape studies of the Si(LVV) transition from this laboratory [16], where the maximum surface hydrogen coverage derived from PH_X adsorbed species has been observed to occur at ~500 K. It also correlates very well the observed drop in the H $^+$ ESD yield from PH_X(a) above ~400 K in the same work [16], as PH₂(a) species dissociate.

Further heating of the Si(111) surface results in the desorption of $H_2(g)$ between 650 - 850 K, leaving only P(a) on the surface as determined by Auger measurements. The quality of the HREEL spectra in the temperature regime (900 - 1000 K) is rather poor, suggesting disorder on the surface. The spectral feature at ~450 cm⁻¹ agrees with the literature value for an Si-P stretching vibration [31] while the origin of the weak feature at ~900 cm⁻¹ is less clear. It may belong to some subsurface Si-P vibrational mode(s), since both features at ~450 and ~900 cm⁻¹ are enhanced after several heating-PH₃ readsorption cycles

between 80 and 900 K (not shown), where an increasing phosphorus concentration is seen with AES measurements. These AES studies have shown that there is evidence for substantial P penetration into the near surface region under these heating-readsorption conditions [17].

3. Adsorption of phosphine on Si(111)-(7x7) at 300 K

Yu and Meyerson [4] have reported PH3 adsorption studies on the Si(100) surface at room temperature with an initial sticking coefficient S_0 of the order of unity. Based on further XPS and thermal desorption studies, Yu et al [5] have suggested that PH3 adsorbs mostly undissociatively on Si(100) at room temperature. In contrast to the behavior reported on Si(100), both the Auger measurements in this work on Si(111)-(7x7), and previous kinetic uptake measurements [32], indicated a reduced overall sticking efficiency for PH3 adsorption on Si(111)-(7x7) at 300 K. The initial sticking coefficient, S_0 , at 300 K, was determined to be 0.26 based upon uptake measurements [32]. HREELS measurements at 300 K clearly indicate a PH3 dissociative adsorption process on Si(111)-(7x7) producing Si-H on the surface.

IV. Summary

We provide vibrational spectroscopic evidence for the dissociative adsorption of PH3 on Si(111)-(7x7) at 80 K. The Si-H species is observed to be produced upon PH3 adsorption. Depending upor the surface coverage, $PH_3(a)$ (minority species) and $PH_2(a)$ species are found on surface. The thermal dissociation of the surface PH_2 species occurs between 450 and 500 K, resulting in the capture of additional hydrogen and phosphorus on the surface.

V. Acknowledgement

We gratefully acknowledge the support of this work by the Office of Naval Research.

References

- 1. A.J. Van Bommel and F. Meyer, Surf. Sci., 8 (1967) 381.
- A.J. Van Bommel and J. Crombeen, Surf. Sci., 36 (1973) 773.
- 3. B.S. Meyerson and W. Olbricht, J. Electrochem. Soc., 131 (1984) 2361.
- 4. M.L. Yu and B.S. Meyerson, J. Vac. Sci. Technol., A2 (1984) 446.
- M.L. Yu, D.J. Vitkavage and B.S. Meyerson, J. Appl. Phys., 59 (1986) 4032.
- 6. M. Nishijima, J. Yoshinobu, H. Tsuda and M. Onchi, Surf. Sci., 192 (1987) 383.
- J. Yoshinobu, H. Tsuda. M. Onchi and M. Nishijima, Chem. Phys. Lett., 130 (1986) 170; Solid State Commun., 60 (1986) 801; J. Chem. Phys., 87 (1987) 7332.
- 8. M. J. Bozack, W.J. Choyke L. Muehlhoff and J.T. Yates, Jr., Surf. Sci., 176 (1986) 547.
- 9. M.J. Bozack, P.A. Taylor, W.J. Choyke and J.T. Yates, Jr., Surf. Sci., 177 (1986) L933.
- 10. C.C. Cheng, R.M. Wallace, P.A. Taylor, W.J. Choyke and J.T. Yates, Jr., J. Appl. Phys., 67 (1990) 3693.
- 11. S. Tanaka, M. Onchi and M. Nishijima, Surf. Sci. 191 (1987) L756.
- 12. D.G. Kilday, G. Margaritondo, D.J. Frankel, J. Anderson and G.J. Lapeyre, Phys. Rev. B, 35 (1987) 9364.
- 13. M. Fujisawa, Y. Taguchi, Y. Kuwahara, M. Onchi and M. Nishijima, Phys. Rev. B, 39 (1989) 12918.
- 14. P.A. Taylor, R.M. Wallace, W.J. Choyke, M.J. Dresser and J.T. Yates, Jr., Surf. Sci., 215 (1989) L286.
- 15. M.J. Dresser, P.A. Taylor, R.M. Wallace, W.J. Choyke and J.T. Yates, Jr., Surf. Sci., 218 (1989) 75.

- 16. R.M. Wallace, P.A. Taylor, W.J. Choyke and J.T. Yates, Jr., submitted, J. Appl. Phys.
- 17. P.A. Taylor, R.M. Wallace, W.J. Choyke and J.T. Yates, Jr., submitted, Surf. Sci.
- 18. J.E. Crowell, J.G. Chen and J.T. Yates, Jr., Surf. Sci., 165 (1986) 37.
- 19. P.J. Chen, M.L. Colaianni and J.T. Yates, Jr., J. Vac. Sci. Technol., A8 (1990) 764.
- 20. M.J. Bozack, L. Muehlhoff, J.N. Russell, Jr., W.J. Choyke and J.T. Yates, Jr., J. Vac. Sci. Technol., A5 (1987) 1.
- 21. J.E. Lamuth, B.N.J. Persson and A.J. Schell-Sorokin, Phys. Rev. Lett., 51 (1983) 2214.
- 22. For a review, see H. Froitzheim, The Chemical Physics of Solid Surfaces and Heterogeneous Catalysis Vol.5, Edited by D.A. King and D.P. Woodruff (Elsevier, Amsterdam, 1988).
- 23. G.E. Mitchell, M.A. Henderson and J.M. White, Surf. Sci., 191 (1987) 425.
- 24. B.A. Sexton and G.E. Mitchell, Surf. Sci., 99 (1980) 523.
- 25. E.R. Nixon, J. Phys. Chem., 60 (1955) 1054; H.R. Linton and E.R. Nixon, Spectrochim. Acta, 15 (1959) 146.
- 26. S.D. Gokhale and W.J. Jolly, Inorg. Chem., 3 (1964) 1141.
- 27. H.C. Beachell and B. Katlafsky, J. Chem. Phys., 27 (1957) 182.
- 28. R.W. Rudolph and R.W. Parry, Inorg. Chem., 4 (1965) 1339.
- 29. S.N. Nabi and N. Sheppard, J. Chem. Soc., (1959) 3439.
- 30. K.B. Mallion, F.G. Mann, B.P. Tong and V.P. Wystrach, J. Chem. Soc., (1963) 1327.
- 31. For a review, see D.E.C. Corbridge, Topics in Phosphorus Chemistry, Vol.6, Edited by M. Grayson and E.J. Griffith (Interscience, New York, 1969).
- 32. R.M. Wallace and P.A. Taylor, unpublished data.

Figure Captions

- Figure 1. HREEL spectra from (a) clean and (b) (e) PH₃-exposed Si(111)-(7x7) surface at 80 K. The PH₃ exposures were as follows (in units of PH₃ molecules/cm²): (b) $5x10^{13}$, (c) $1x10^{14}$, (d) $1x10^{15}$ and (e) $2x10^{15}$.
- Figure 2. Thermal desorption spectra of all the desorbing species observed from $PH_3/Si(111)-(7x7)$. The temperature ramp used in these studies was $dT/dt = 1.6 \text{ K sec}^{-1}$. Comparision of the integrated area of the PH_3 desorption trace to that of H_2 suggests that the observed $PH_3(g)$ corresponds only to a small fraction of a monolayer.
- Figure 3. HREEL spectra of PH $_3$ /Si(111)-(7x7) at 80 K after heating to various temperatures and cooling to 80 K. The initial saturation exposure of PH $_3$ was $2x10^{15}$ PH $_3$ molecules/cm 2 .

<u>РН3</u>		PH3(g)(a)	PH3/Pt(111)(b)	·	
	ν _s (PH ₃)	2328 cm ⁻¹	2325 cm ⁻¹		
	vd(PH3)	2323	2325		
	δ _s (PH ₃)	991	985		
	δ _d (PH ₃)	1121	1080		
	v(PtP)		370		
- PH ₂	(DU.)		P ₂ H ₄ (c)		
			2312 cm ⁻¹		
	-	1069 454	1081	1093	1073 475-515
<u>> PH</u>		(CH ₃) ₂ PH(e)	F ₂ PH(f)	(CF ₃) ₂ PH(g)	(CF ₃ S) ₂ PH(g)
	v(PH)	2289 cm ⁻¹	2240 cm ⁻¹	2300 cm ⁻¹	2320 cm ⁻¹
	δ(PH)	998	1016	850	894

```
a ref. [31]
```

i this work

b ref. [23]

c ref. [25]

d ref. [26]

e ref. [27]

f ref. [28]

g ref. [29]

h ref. [30]: here R_1 = substituted Ph group; R_2 = Ph group

HREEL Spectra of PH₃/Si(111) at Various Coverages

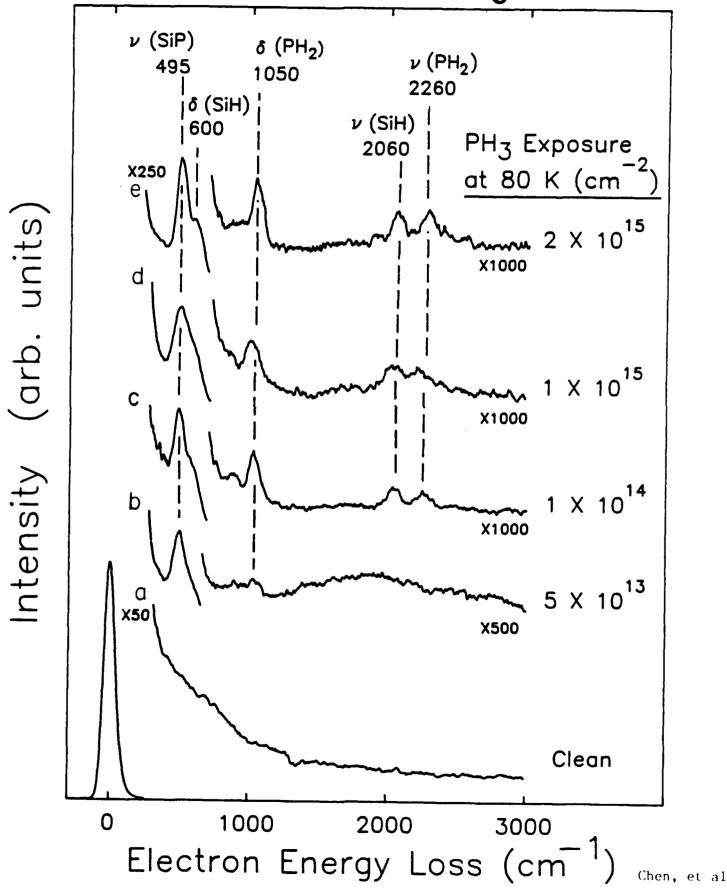
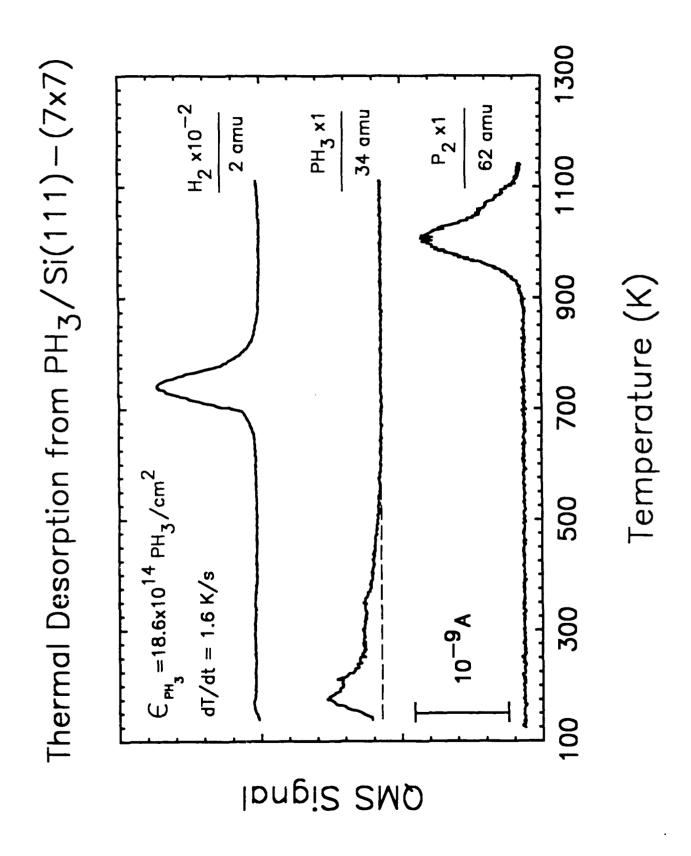
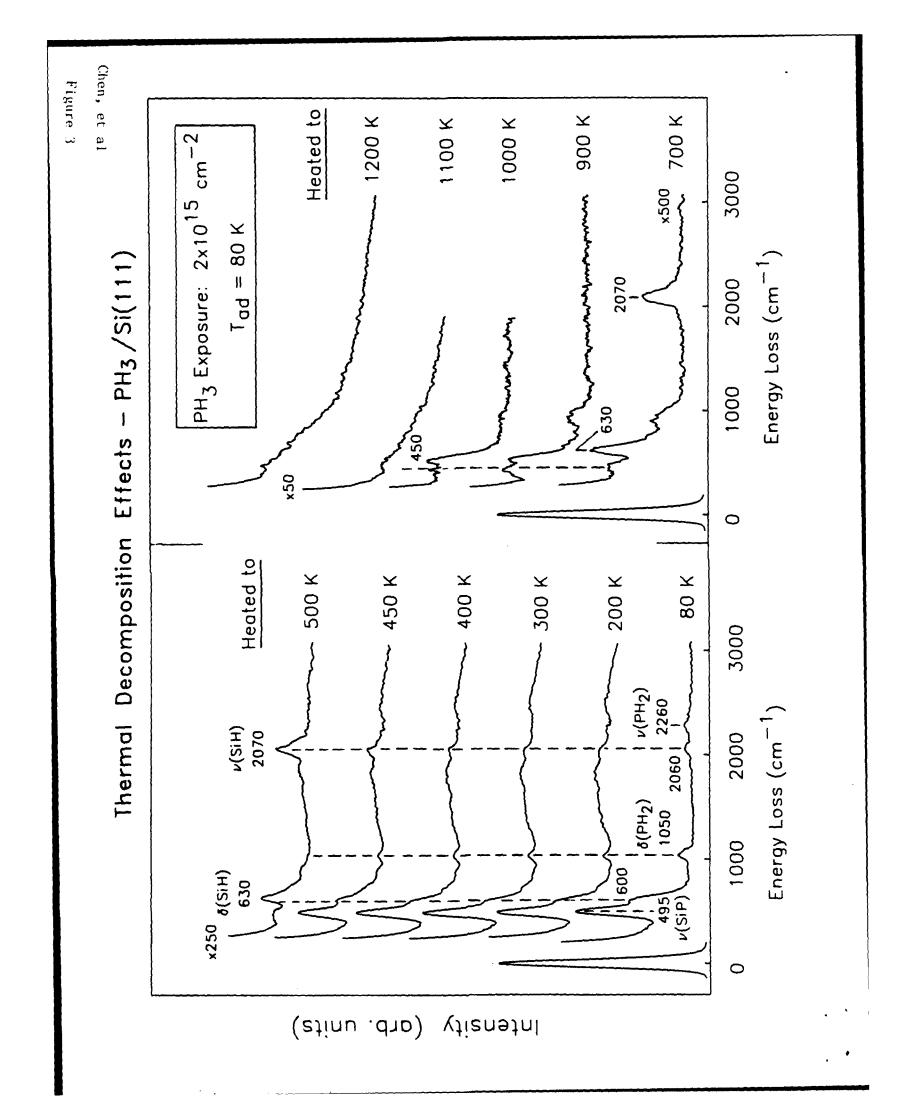


Figure 1





TECHNICAL REPORT DISTRIBUTION LIST - GENERAL

- Office of Naval Research (2) Chemistry Division, Code 1113 800 North Quincy Street Arlington, Virginia 22217-5000
- Commanding Officer (1)
 Naval Weapons Support Center
 Dr. Bernard E. Douda
 Crane, Indiana 47522-5050
- Dr. Richard W. Drisko (1)
 Naval Civil Engineering
 Laboratory
 Code L52
 Port Hueneme, CA 93043
- David Taylor Research Center (1) Dr. Eugene C. Fischer Annapolis, MD 21402-5067
- Dr. James S. Murday (1) Chemistry Division, Code 6100 Naval Research Laboratory Washington, D.C. 20375-5000

Defense Technical Information Center (2) Building 5, Cameron Station Alexandria, VA 22314

- Dr. Robert Graen, Director (1) Chemistry Division, Code 385 Naval Weapons Center China Lake, CA 93555-6001
- Chief of Naval Research (1)
 Special Assistant for Marine
 Corps Matters
 Code 00MC
 800 North Quincy Street
 Arlington, VA 22217-5000
- Dr. Bernadette Eichinger (1)
 Naval Ship Systems Engineering
 Station
 Code 053
 Philadelphia Naval Base
 Philadelphia, PA 19112
- Dr. Sachio Yamamoto (1)
 Naval Ocean Systems Center
 Code 52
 San Diego, CA 92152-5000
- Dr. Harold H. Singerman (1)
 David Taylor Research Center
 Code 283
 Annapolis, MD 21402-5067